

B1
C1

5. (amended) The method of claim 1, wherein said silicon-containing structure is a bottom electrode of a storage capacitor of a memory device and said nitrided portion of said silicon-containing structure is a capacitor dielectric.

Sub
C3
B2

7. (amended) A method of forming an electrical device which has a dielectric formed between a bottom structure and a top structure, said method comprising the steps of:

— providing said bottom structure;
— providing a nitrogen-containing gas over said bottom structure;
— heating said bottom structure at an ambient temperature which is at least 900C;

— [providing] creating a plasma over said bottom structure to cause thermal nitridation of said bottom structure so as to form said dielectric over said bottom structure; and

— providing said top structure over said dielectric.

Please add the following claim:

--13. A method of forming a gate dielectric layer on a semiconductor substrate, said method comprising the steps of:

— providing a nitrogen-containing gas;

— heating said silicon-containing structure to an elevated temperature which is greater than 900°C;

— subjecting said semiconductor substrate to a plasma, wherein the combination of said nitrogen-containing gas, said elevated temperature, and said plasma result in the thermal nitridation of a portion of said semiconductor substrate; and

— forming a ^{gate} gate electrode over said nitrided portion of said semiconductor substrate.--

REMARKS